

# MMBV3102LT1G

## Silicon Tuning Diode

This device is designed in the Surface Mount package for general frequency control and tuning applications. It provides solid-state reliability in replacement of mechanical tuning methods.

### Features

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

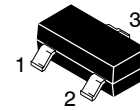
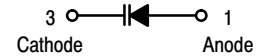
Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	Vdc
Forward Current	I <sub>F</sub>	200	mAdc
Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Junction Temperature	T <sub>J</sub>	+125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



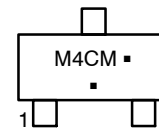
**ON Semiconductor®**

<http://onsemi.com>



**SOT-23 (TO-236)  
CASE 318  
STYLE 8**

### MARKING DIAGRAM



M4C = Specific Device Code

M = Date Code\*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MMBV3102LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBV3102LT1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu\text{A}$ )	$V_{(BR)R}$	30	-	-	Vdc
Reverse Voltage Leakage Current ( $V_R = 25 \text{ Vdc}$ , $T_A = 25^\circ\text{C}$ )	$I_R$	-	-	0.1	$\mu\text{A}$
Diode Capacitance Temperature Coefficient ( $V_R = 4.0 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )	$TC_C$	-	300	-	ppm/ $^\circ\text{C}$

Device	$C_T$ , Diode Capacitance $V_R = 3.0 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ pF			$Q$ , Figure of Merit $V_R = 3.0 \text{ Vdc}$ $f = 50 \text{ MHz}$	$C_R$ , Capacitance Ratio $C_3/C_{25}$ $f = 1.0 \text{ MHz}$	
	Min	Nom	Max	Min	Min	Typ
MMBV3102LT1	20	22	25	200	4.5	4.8

## TYPICAL CHARACTERISTICS

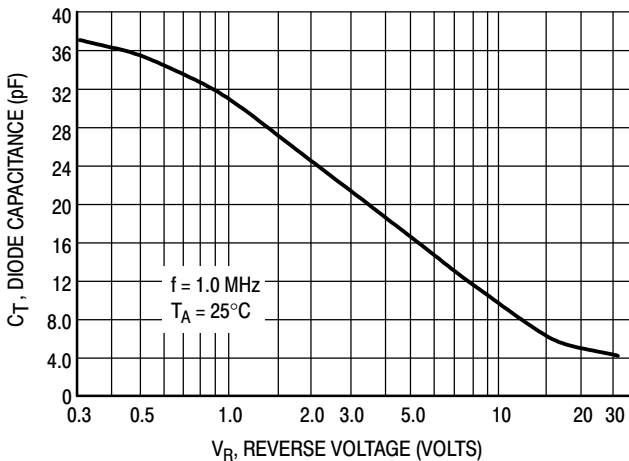


Figure 1. Diode Capacitance

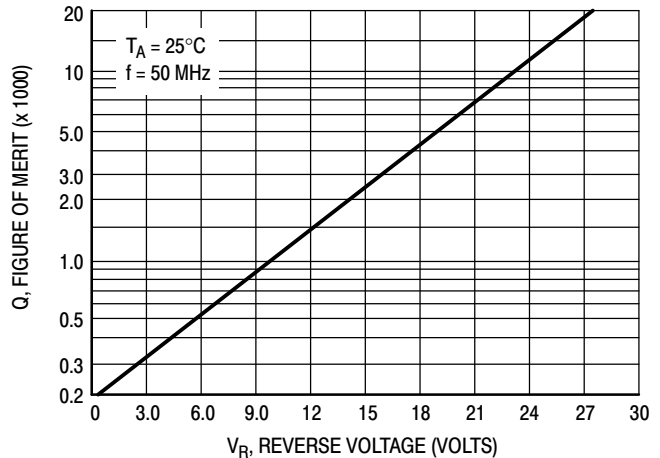


Figure 2. Figure of Merit

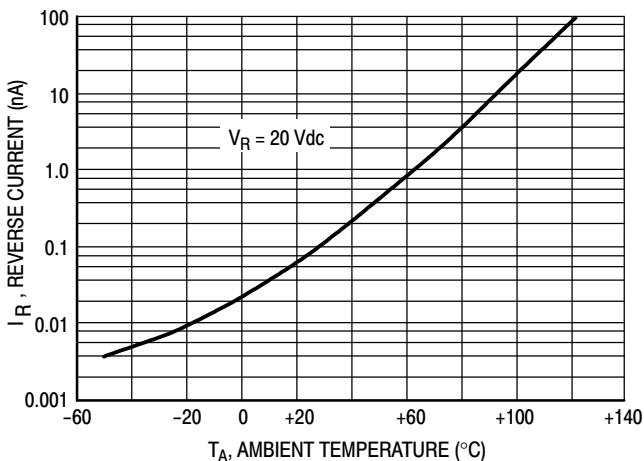


Figure 3. Leakage Current

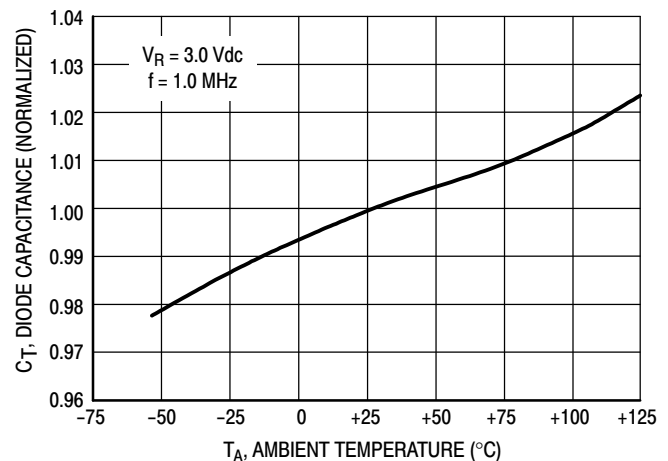


Figure 4. Diode Capacitance

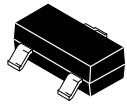
## NOTES ON TESTING AND SPECIFICATIONS

- $C_R$  is the ratio of  $C_T$  measured at 3.0 Vdc divided by  $C_T$  measured at 25 Vdc.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

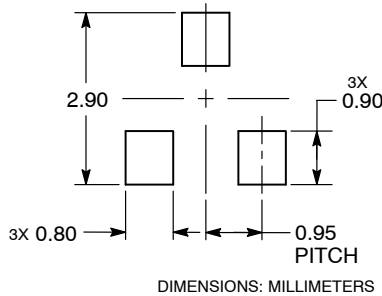


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

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